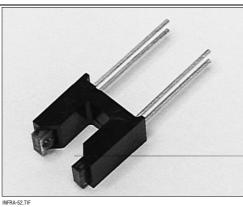
### **HOA0825 Transmissive Sensor**

FEATURES

- Phototransistor output
- Four mounting configurations
- 0.165 in.(4.2 mm) slot width



DESCRIPTION

The HOA0825 series consists of an infrared emitting diode facing an NPN silicon phototransistor encased in a black thermoplastic housing. A slot in the housing between emitter and detector provides the means for mechanically interrupting the emitter beam. The phototransistor switching takes place whenever an opaque object passes through the slot between emitter and detector. The HOA0825 series employs plastic molded components. For additional component information see SEP8506 and SDP8406.

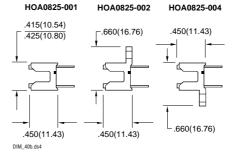


Housing material is polycarbonate. Housings are soluble in chlorinated hydrocarbons and ketones. Recommended cleaning agents are methanol and isopropanol.

OUTLINE DIMENSIONS in inches (mm) Tolerance 3 plc decimals ±0.010(0.25) ±0.020(0.51)

2 plc decimals

HOA0825-003 .406(10.31) .250(6.35) NOTCH INDICATES COLLECTOR .160(4.06) .125(3.18) .125(3.2) DIA TYP .425(10.80) ТАВ È ا (17.27)680. °C F .300(7.62) .900(22.86) .690(17.53) κA 4 .125(3.18) TAB #2 ŧ. æ 406(10.29) OPTICALC .105(2.67) .095(2.41) .115(2.92) .105(2.67) \_\_.120(3.06) DIM\_040.ds4



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# HOA0825

**Transmissive Sensor** 

ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)								
PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS		
IR EMITTER								
Forward Voltage	VF			1.6	V	l <sub>F</sub> =20 mA		
Reverse Leakage Current	R			10	μA	V <sub>R</sub> =3 V		
DETECTOR								
Collector-Emitter Breakdown Voltage	V(BR)CEO	30			V	Ic=100 μΑ		
Emitter-Collector Breakdown Voltage	V(BR)ECO	5.0			V	I <sub>E</sub> =100 μA		
Collector Dark Current	ICEO			100	nA	V <sub>CE</sub> =10 V, I <sub>F</sub> =0		
COUPLED CHARACTERISTICS On-State Collector Current HOA0825-001, -002, -003, -004	Ic(on)	0.5			mA	Vce=0.5 V I⊧=20 mA		
Collector-Emitter Saturation Voltage	$V_{\text{CE}(\text{SAT})}$			0.4	V	l⊧=20 mA Ic=250 μA		
Rise And Fall Time	tr, t <sub>f</sub>		15		μs	V <sub>CC</sub> =5 V, Ic=1 mA R <sub>L</sub> =1000 Ω		

### ABSOLUTE MAXIMUM RATINGS

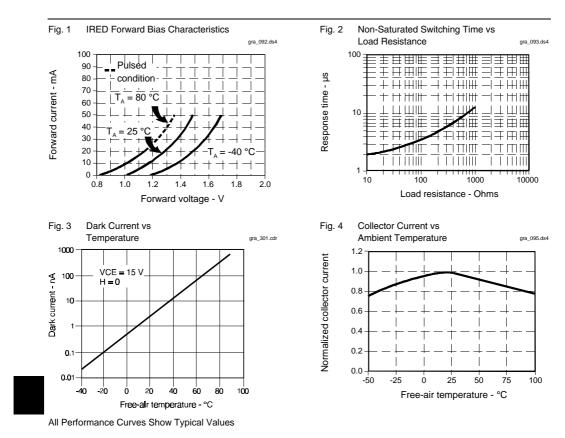
(25°C Free-Air Temperature unless otherwise	noted)
Operating Temperature Range	-40°C to 85°C
Storage Temperature Range	-40°C to $85^{\circ}C$
Soldering Temperature (5 sec)	240°C
IR EMITTER	
Power Dissipation	100 mW (1)
Reverse Voltage	3 V
Continuous Forward Current	50 mA
DETECTOR	
Collector-Emitter Voltage	30 V
Emitter-Collector Voltage	5 V
Power Dissipation	100 mW (1)
Collector DC Current	30 mA

SCHEMATIC Anode Collector

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